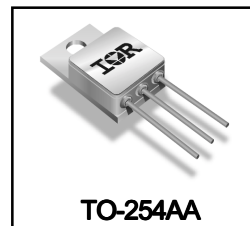


**RADIATION HARDENED  
POWER MOSFET  
THRU-HOLE (TO-254AA)**

**IRHM7150  
JANSR2N7268  
100V, N-CHANNEL  
REF: MIL-PRF-19500/603  
RAD Hard™ HEXFET® TECHNOLOGY**

**Product Summary**

Part Number	Radiation Level	RDS(on)	ID	QPL Part Number
IRHM7150	100K Rads (Si)	0.065Ω	34A	JANSR2N7268
IRHM3150	300K Rads (Si)	0.065Ω	34A	JANSF2N7268
IRHM4150	600K Rads (Si)	0.065Ω	34A	JANSF2N7268
IRHM8150	1000K Rads (Si)	0.065Ω	34A	JANSH2N7268



International Rectifier's RADHard HEXFET® technology provides high performance power MOSFETs for space applications. This technology has over a decade of proven performance and reliability in satellite applications. These devices have been characterized for both Total Dose and Single Event Effects (SEE). The combination of low Rds(on) and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching, ease of paralleling and temperature stability of electrical parameters.

**Features:**

- Single Event Effect (SEE) Hardened
- Low RDS(on)
- Low Total Gate Charge
- Proton Tolerant
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Ceramic Eyelets
- Light Weight

**Absolute Maximum Ratings**

**Pre-Irradiation**

	Parameter		Units
ID @ VGS = 12V, TC = 25°C	Continuous Drain Current	34	A
ID @ VGS = 12V, TC = 100°C	Continuous Drain Current	21	
IDM	Pulsed Drain Current ①	136	
PD @ TC = 25°C	Max. Power Dissipation	150	W
	Linear Derating Factor	1.2	W/°C
VGS	Gate-to-Source Voltage	±20	V
EAS	Single Pulse Avalanche Energy ②	500	mJ
IAR	Avalanche Current ①	34	A
EAR	Repetitive Avalanche Energy ①	15	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.5	V/ns
TJ	Operating Junction	-55 to 150	°C
TSTG	Storage Temperature Range		
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)	
	Weight	9.3 (Typical)	g

For footnotes refer to the last page

**Electrical Characteristics @ Tj = 25°C (Unless Otherwise Specified)**

	Parameter	Min	Typ	Max	Units	Test Conditions
BVDSS	Drain-to-Source Breakdown Voltage	100	—	—	V	VGS = 0V, ID = 1.0mA
ΔBVDSS/ΔTj	Temperature Coefficient of Breakdown Voltage	—	0.13	—	V/°C	Reference to 25°C, ID = 1.0mA
RDS(on)	Static Drain-to-Source On-State Resistance	—	—	0.065	Ω	VGS = 12V, ID = 21A
		—	—	0.076		VGS = 12V, ID = 34A ④
VGS(th)	Gate Threshold Voltage	2.0	—	4.0	V	VDS = VGS, ID = 1.0mA
gfs	Forward Transconductance	8.0	—	—	S (τ)	VDS > 15V, IDS = 21A ④
IDSS	Zero Gate Voltage Drain Current	—	—	25	μA	VDS = 80V, VGS = 0V
		—	—	250		VDS = 80V VGS = 0V, Tj = 125°C
IGSS	Gate-to-Source Leakage Forward	—	—	100	nA	VGS = 20V
IGSS	Gate-to-Source Leakage Reverse	—	—	-100		VGS = -20V
Qg	Total Gate Charge	—	—	160	nC	VGS = 12V, ID = 34A VDS = 50V
Qgs	Gate-to-Source Charge	—	—	35		
Qgd	Gate-to-Drain ('Miller') Charge	—	—	65		
td(on)	Turn-On Delay Time	—	—	45	ns	VDD = 50V, ID = 14A, VGS = 12V, RG = 2.35Ω
tr	Rise Time	—	—	190		
td(off)	Turn-Off Delay Time	—	—	170		
tf	Fall Time	—	—	130		
LS + LD	Total Inductance	—	6.8	—	nH	Measured from drain lead (6mm/0.25in. from package) to source lead (6mm/0.25in. from package)
Ciss	Input Capacitance	—	4300	—	pF	VGS = 0V, VDS = 25V f = 1.0MHz
Coss	Output Capacitance	—	1200	—		
Crss	Reverse Transfer Capacitance	—	200	—		

**Source-Drain Diode Ratings and Characteristics**

	Parameter	Min	Typ	Max	Units	Test Conditions
IS	Continuous Source Current (Body Diode)	—	—	34	A	
ISM	Pulse Source Current (Body Diode) ①	—	—	136		
VSD	Diode Forward Voltage	—	—	1.4	V	Tj = 25°C, IS = 34A, VGS = 0V ④
trr	Reverse Recovery Time	—	—	570	nS	Tj = 25°C, IF = 34A, di/dt ≤ 100A/μs VDD ≤ 50V ④
QRR	Reverse Recovery Charge	—	—	5.8	μC	
ton	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by LS + LD.				

**Thermal Resistance**

	Parameter	Min	Typ	Max	Units	Test Conditions
RthJC	Junction-to-Case	—	—	0.83	°C/W	Typical socket mount
RthCS	Case-to-sink	—	0.21	—		
RthJA	Junction-to-Ambient	—	—	48		

**Note: Corresponding Spice and Saber models are available on the G&S Website.**

For footnotes refer to the last page

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

**Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation** ⑤⑥

	Parameter	100K Rads (Si) <sup>1</sup>		300 to 1000K Rads (Si) <sup>2</sup>		Units	Test Conditions
		Min	Max	Min	Max		
BVDSS	Drain-to-Source Breakdown Voltage	100	—	100	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1.0mA
V <sub>GS(th)</sub>	Gate Threshold Voltage ④	2.0	4.0	1.25	4.5		V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 1.0mA
I <sub>GSS</sub>	Gate-to-Source Leakage Forward	—	100	—	100	nA	V <sub>GS</sub> = 20V
I <sub>GSS</sub>	Gate-to-Source Leakage Reverse	—	-100	—	-100		V <sub>GS</sub> = -20 V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	—	25	—	50	μA	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V
R <sub>DS(on)</sub>	Static Drain-to-Source ④ On-State Resistance (TO-3)	—	0.065	—	0.09	Ω	V <sub>GS</sub> = 12V, I <sub>D</sub> =21A
R <sub>DS(on)</sub>	Static Drain-to-Source ④ On-State Resistance (TO-254AA)	—	0.065	—	0.09	Ω	V <sub>GS</sub> = 12V, I <sub>D</sub> =21A
V <sub>SD</sub>	Diode Forward Voltage ④	—	1.4	—	1.4	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 34A

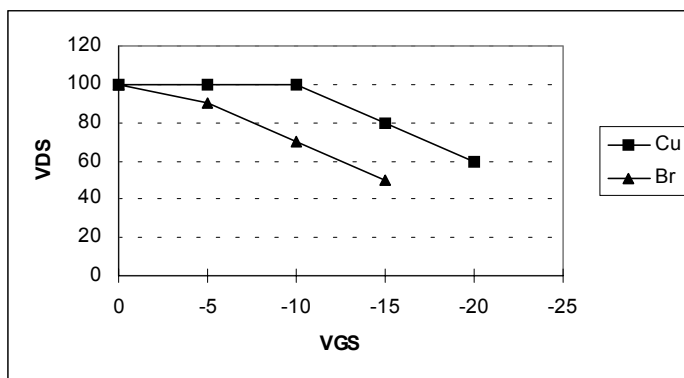
1. Part number IRHM7150 (JANSR2N7268)

2. Part numbers IRHM3150 (JANSF2N7268), IRHM4150 (JANSJ2N7268) and IRHM8150 (JANSH2N7268)

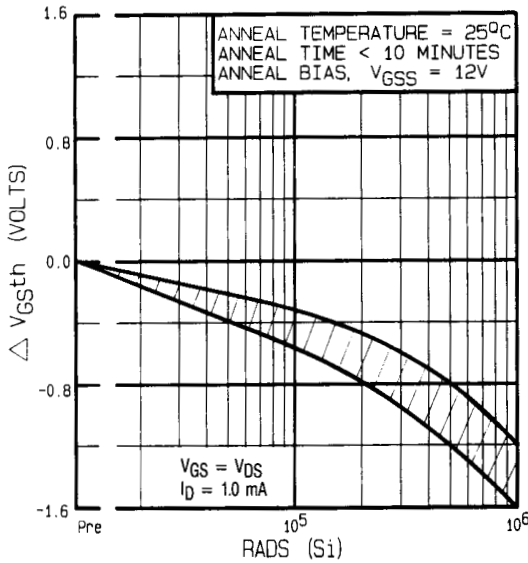
International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

**Table 2. Single Event Effect Safe Operating Area**

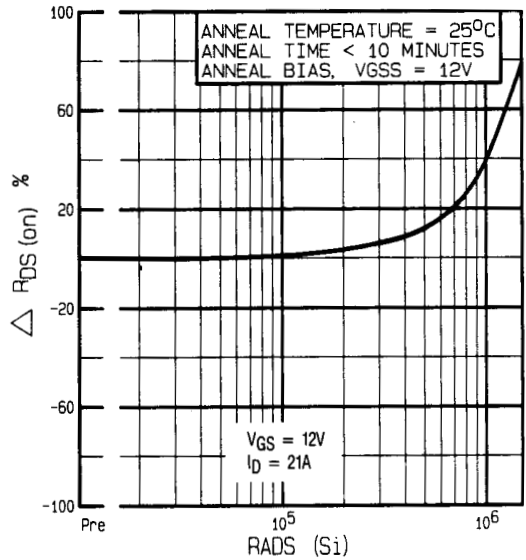
Ion	LET MeV/(mg/cm <sup>2</sup> )	Energy (MeV)	Range (μm)	VDS(V)					
				@VGS=0V	@VGS=-5V	@VGS=-10V	@VGS=-15V	@VGS=-20V	@VGS=-25V
Cu	28	285	43	100	100	100	80	60	—
Br	36.8	305	39	100	90	70	50	—	—



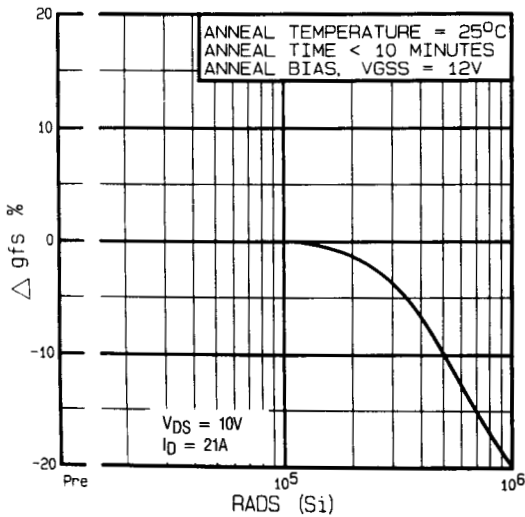
**Fig a. Single Event Effect, Safe Operating Area**



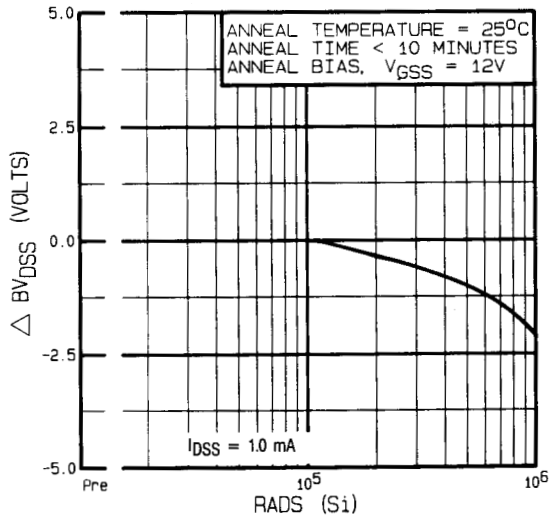
**Fig 1.** Typical Response of Gate Threshold Voltage Vs. Total Dose Exposure



**Fig 2.** Typical Response of On-State Resistance Vs. Total Dose Exposure



**Fig 3.** Typical Response of Transconductance Vs. Total Dose Exposure



**Fig 4.** Typical Response of Drain to Source Breakdown Vs. Total Dose Exposure

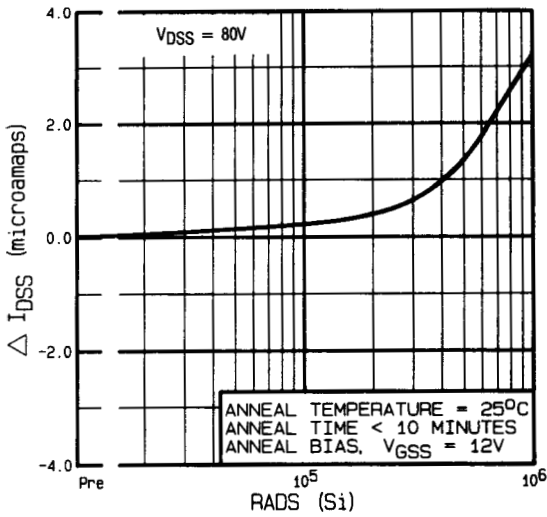


Fig 5. Typical Zero Gate Voltage Drain Current Vs. Total Dose Exposure

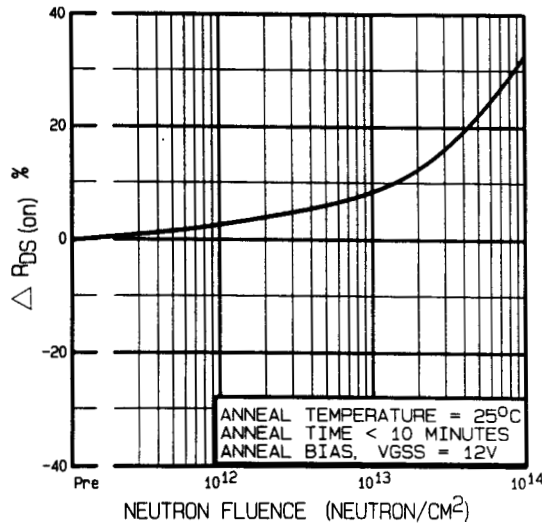


Fig 6. Typical On-State Resistance Vs. Neutron Fluence Level

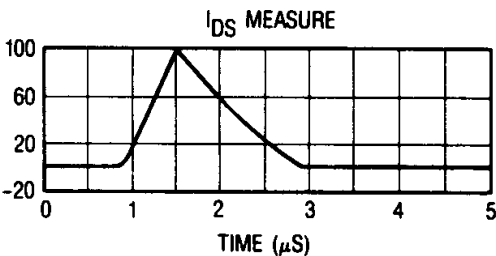
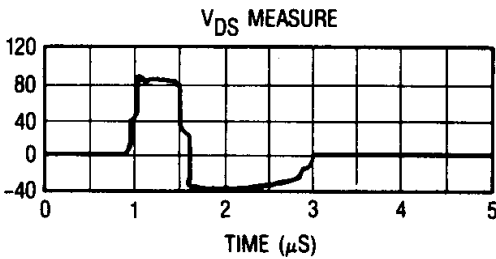


Fig 7. Typical Transient Response of Rad Hard HEXFET During  $1 \times 10^{12}$  Rad (Si)/Sec Exposure

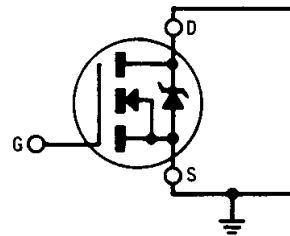


Fig 8a. Gate Stress of  $V_{GSS}$  Equals 12 Volts During Radiation

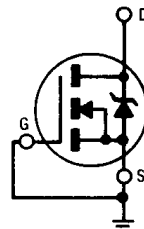


Fig 8b.  $V_{DSS}$  Stress Equals 80% of  $B_{DSS}$  During Radiation  
www.DataSheet4U.com

Note: Bias Conditions during radiation:  $V_{GS} = 12\text{ Vdc}$ ,  $V_{DS} = 0\text{ Vdc}$

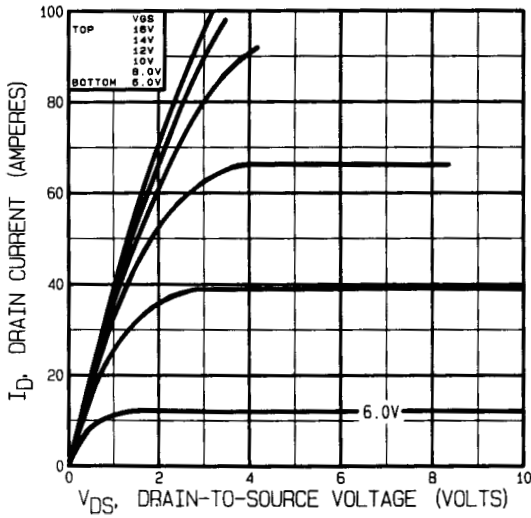


Fig 9. Typical Output Characteristics Pre-Irradiation

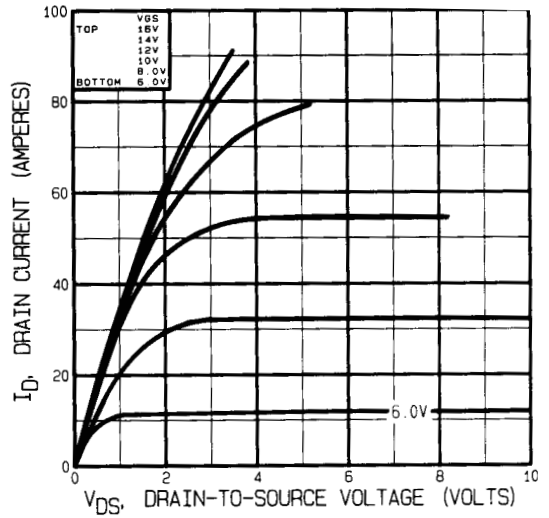


Fig 10. Typical Output Characteristics Post-Irradiation 100K Rads (Si)

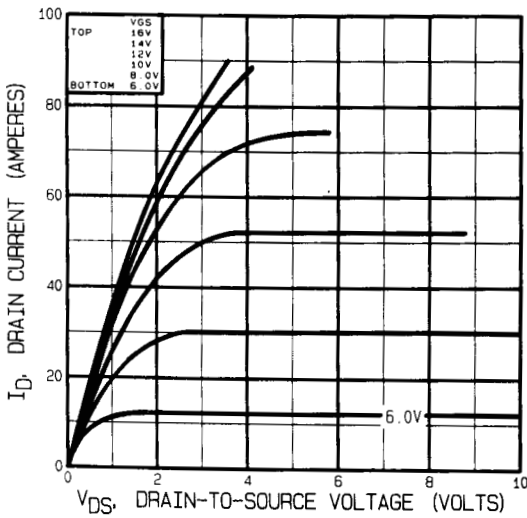


Fig 11. Typical Output Characteristics Post-Irradiation 300K Rads (Si)

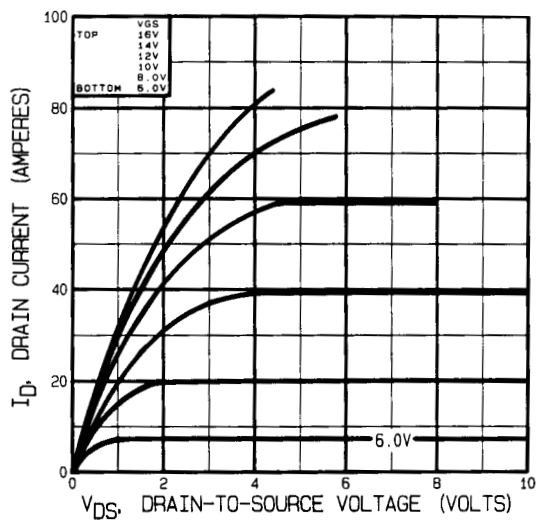


Fig 12. Typical Output Characteristics Post-Irradiation 1 Mega Rads (Si)

Note: Bias Conditions during radiation:  $V_{GS} = 0$  Vdc,  $V_{DS} = 80$  Vdc

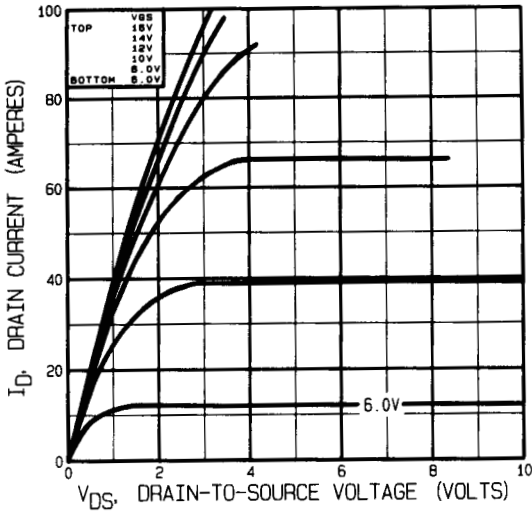


Fig 13. Typical Output Characteristics Pre-Irradiation

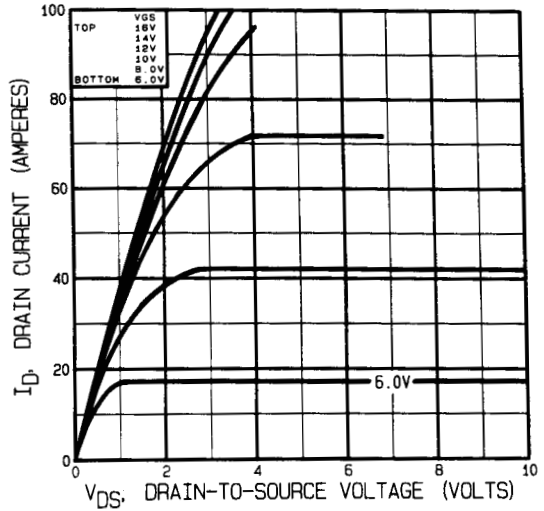


Fig 14. Typical Output Characteristics Post-Irradiation 100K Rads (Si)

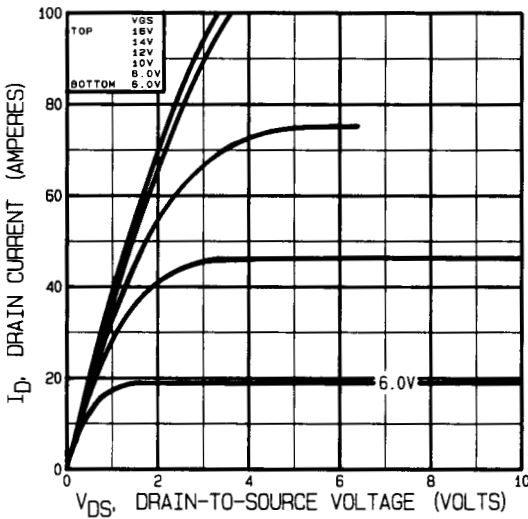


Fig 15. Typical Output Characteristics Post-Irradiation 300K Rads (Si)

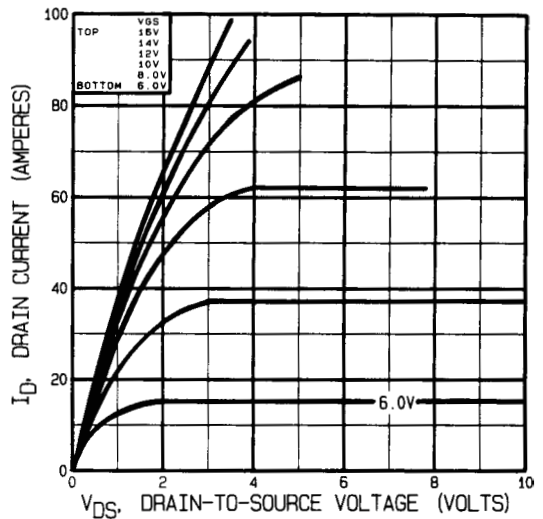


Fig 16. Typical Output Characteristics Post-Irradiation 1 Mega Rads (Si)

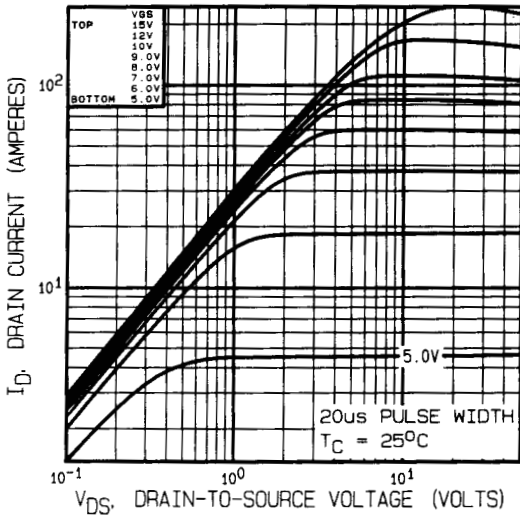


Fig 17. Typical Output Characteristics

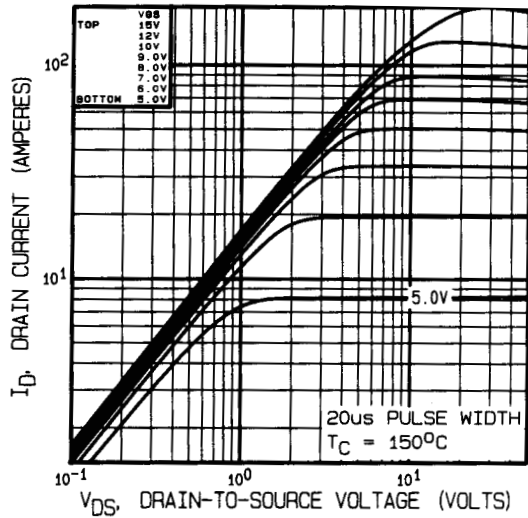


Fig 18. Typical Output Characteristics

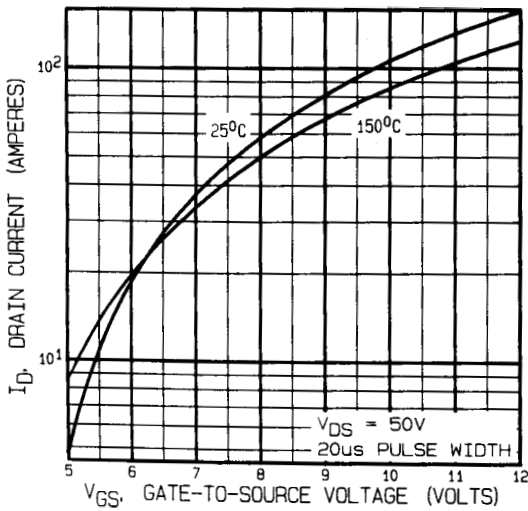


Fig 19. Typical Transfer Characteristics

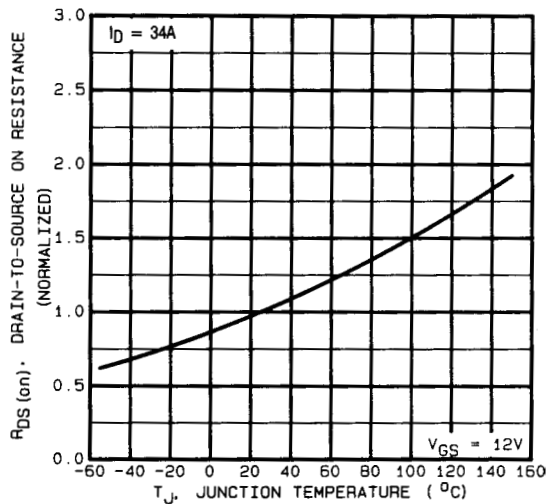


Fig 20. Normalized On-Resistance Vs Temperature



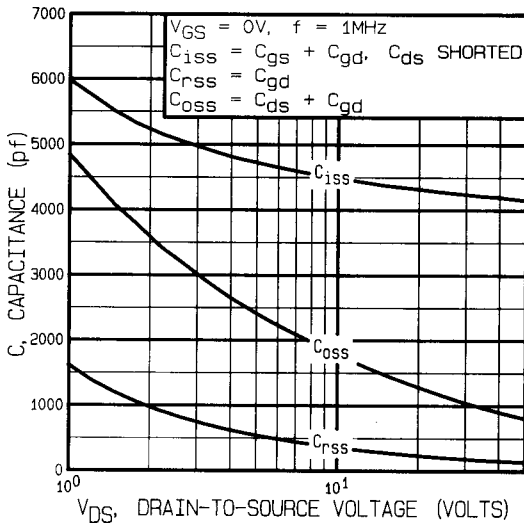


Fig 21. Typical Capacitance Vs. Drain-to-Source Voltage

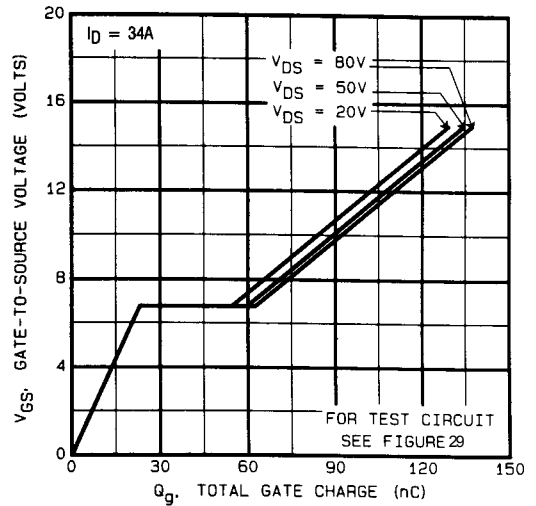


Fig 22. Typical Gate Charge Vs. Gate-to-Source Voltage

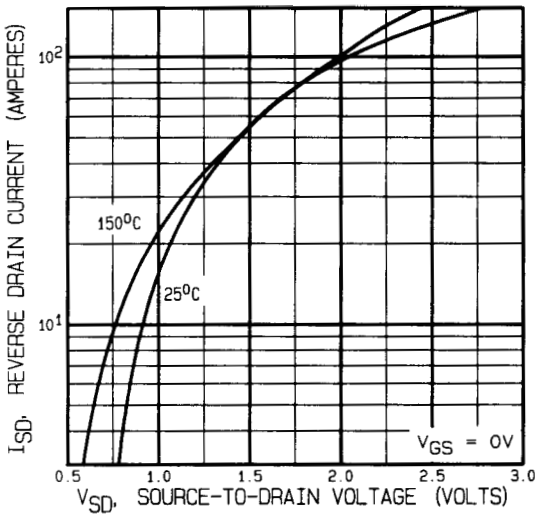


Fig 23. Typical Source-Drain Diode Forward Voltage

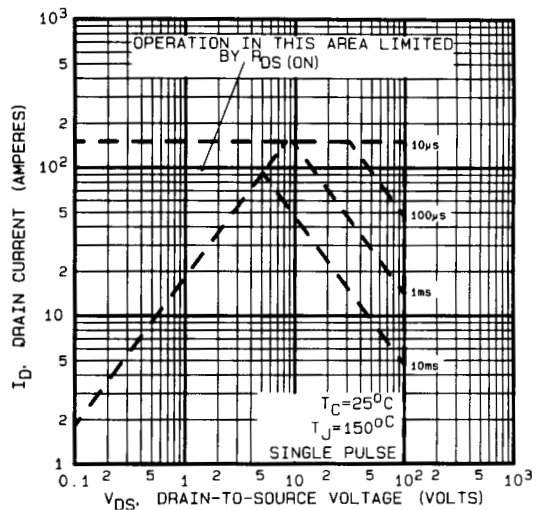
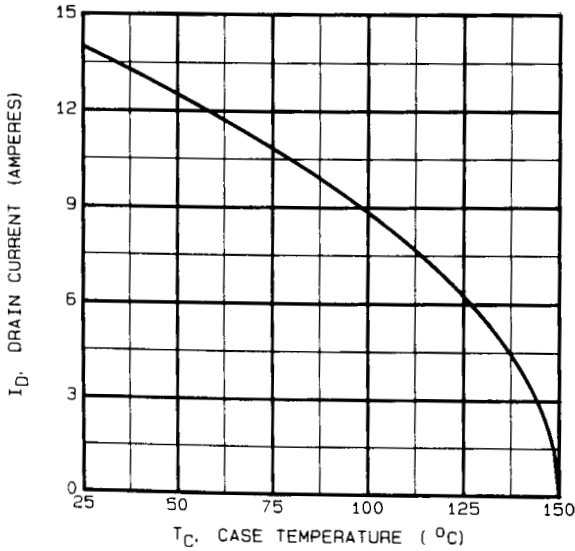
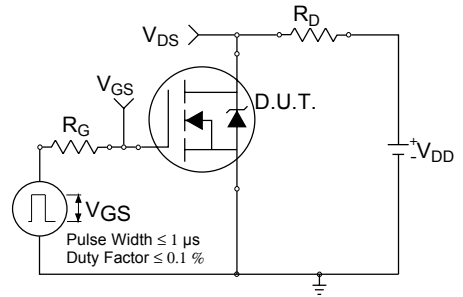


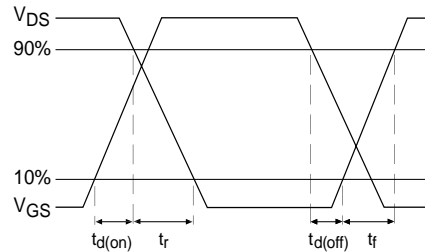
Fig 24. Maximum Safe Operating Area



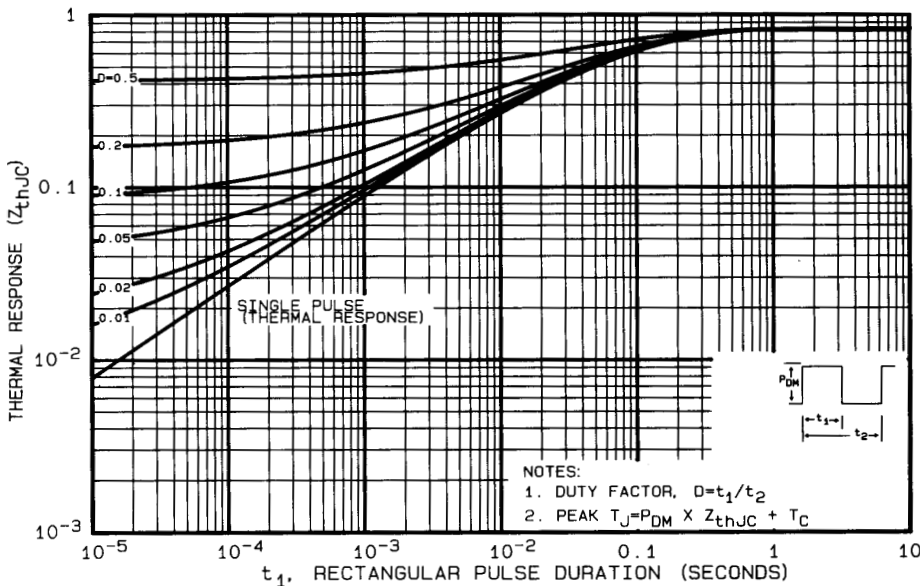
**Fig 25.** Maximum Drain Current Vs. Case Temperature



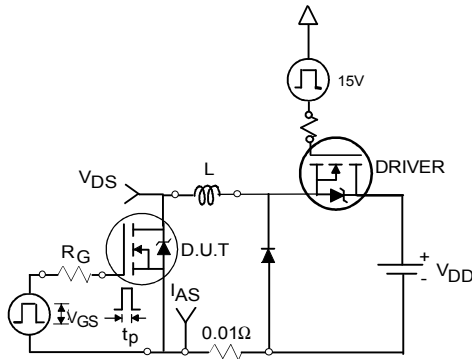
**Fig 26a.** Switching Time Test Circuit



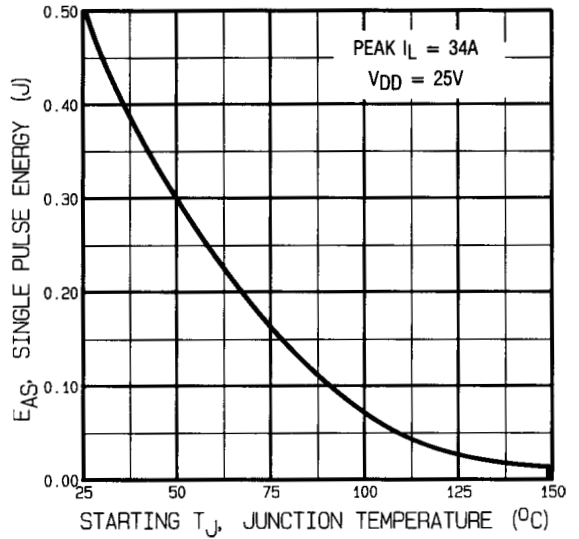
**Fig 26b.** Switching Time Waveforms



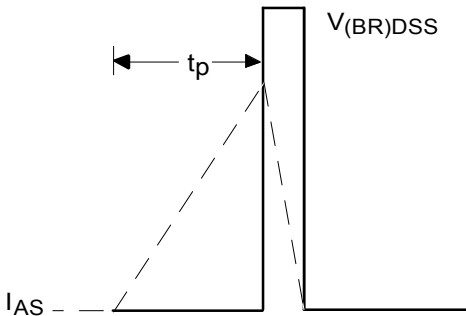
**Fig 27.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



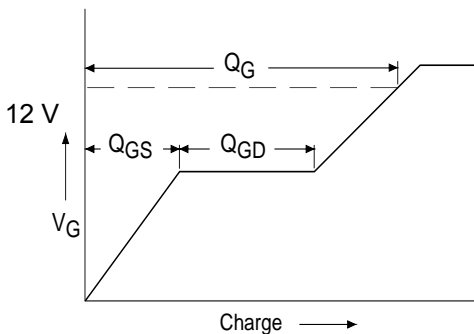
**Fig 28a.** Unclamped Inductive Test Circuit



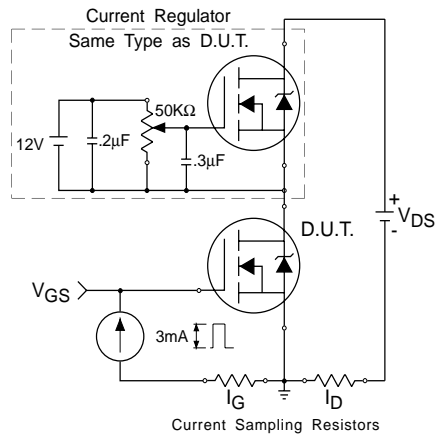
**Fig 28c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 28b.** Unclamped Inductive Waveforms



**Fig 29a.** Basic Gate Charge Waveform

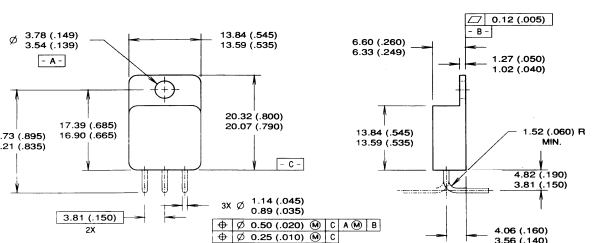
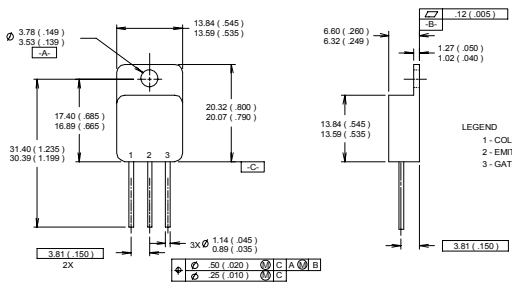


**Fig 29b.** Gate Charge Test Circuit

**Foot Notes:**

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ②  $V_{DD} = 25V$ , starting  $T_J = 25^\circ C$ ,  $L = 0.86mH$   
Peak  $I_L = 26A$ ,  $V_{GS} = 12V$
- ③  $I_{SD} \leq 26A$ ,  $di/dt \leq 190A/\mu s$ ,  
 $V_{DD} \leq 100V$ ,  $T_J \leq 150^\circ C$
- ④ Pulse width  $\leq 300 \mu s$ ; Duty Cycle  $\leq 2\%$
- ⑤ **Total Dose Irradiation with  $V_{GS}$  Bias.**  
12 volt  $V_{GS}$  applied and  $V_{DS} = 0$  during irradiation per MIL-STD-750, method 1019, condition A.
- ⑥ **Total Dose Irradiation with  $V_{DS}$  Bias.**  
80 volt  $V_{DS}$  applied and  $V_{GS} = 0$  during irradiation per MIL-STD-750, method 1019, condition A.

**Case Outline and Dimensions — TO-254AA**



**NOTES:**

- 1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982.
- 2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3. LEADFORM IS AVAILABLE IN EITHER ORIENTATION

**LEGEND**

- 1- DRAIN
- 2- SOURCE
- 3- GATE

**CAUTION**

**BERYLLIA WARNING PER MIL-PRF-19500**

Packages containing beryllia shall not be ground, sandblasted, machined or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.



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Data and specifications subject to change without notice. 08/01

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